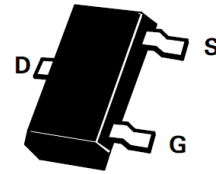


Features

- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q101, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](#) or your local Diodes representative.
- <https://www.diodes.com/quality/product-definitions/>


SOT23

PARTMARKING DETAIL- MX

Absolute Maximum Ratings

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V_{DS}	-45	V
Continuous Drain Current at $T_{amb}=25^{\circ}C$	I_D	-90	mA
Pulsed Drain Current	I_{DM}	-1.6	A
Gate Source Voltage	V_{GS}	± 20	V
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	330	mW
Operating and Storage Temperature Range	$T_j:T_{stg}$	-55 to +150	$^{\circ}C$

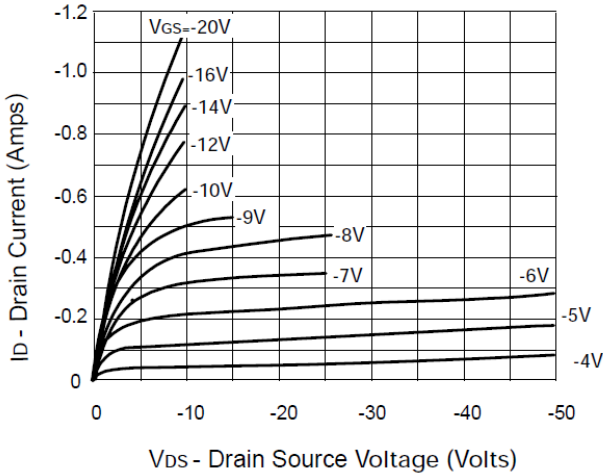
Electrical Characteristics (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV_{DSS}	-45	-70		V	$I_D = -100\mu A, V_{GS} = 0V$
Gate-Source Threshold Voltage	$V_{GS(th)}$	-1		-3.5	V	$I_D = -1mA, V_{DS} = V_{GS}$
Gate-Body Leakage	I_{GSS}			-20	nA	$V_{GS} = -15V, V_{DS} = 0V$
Zero Gate Voltage Drain Current	I_{DSS}			-0.5	μA	$V_{DS} = -25V, V_{GS} = 0V$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		9	14	Ω	$V_{GS} = -10V, I_D = -200mA$
Forward Transconductance (1)(2)	g_{fs}		90		mS	$V_{DS} = -10V, I_D = -200mA$
Input Capacitance (2)	C_{iss}		25		pF	$V_{DS} = -10V, V_{GS} = 0V, f = 1MHz$
Turn-On Delay Time (2)(3)	$t_{d(on)}$			10	ns	$V_{DD} \approx -25V, I_D = -200mA$
Rise Time (2)(3)	t_r			10	ns	
Turn-Off Delay Time (2)(3)	$t_{d(off)}$			10	ns	
Fall Time (2)(3)	t_f			10	ns	

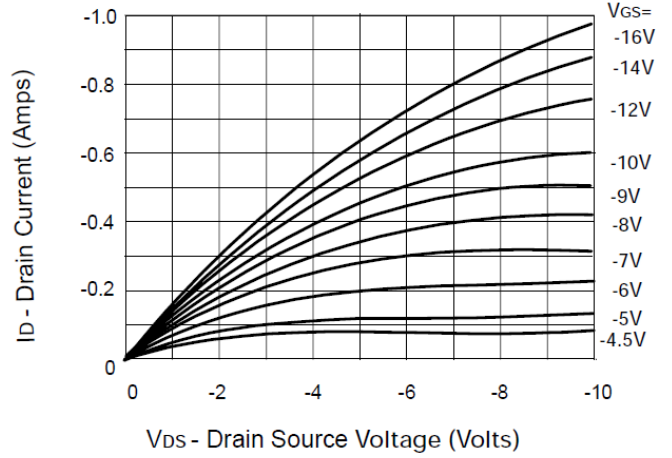
 (1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$ (2) Sample test.

 (3) Switching times measured with 50 Ω source impedance and <5ns rise time on a pulse generator
 Spice parameter data is available upon request for this device

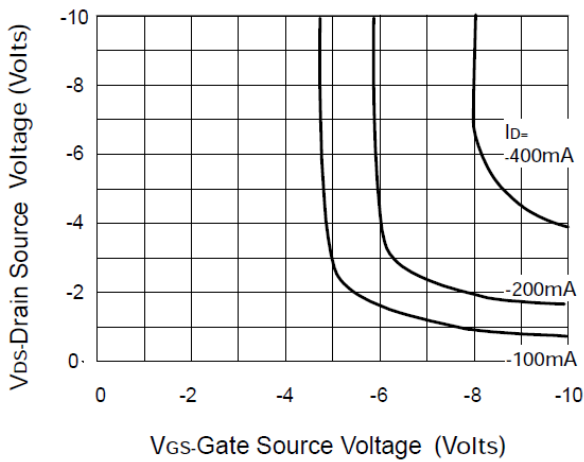
Typical Characteristics



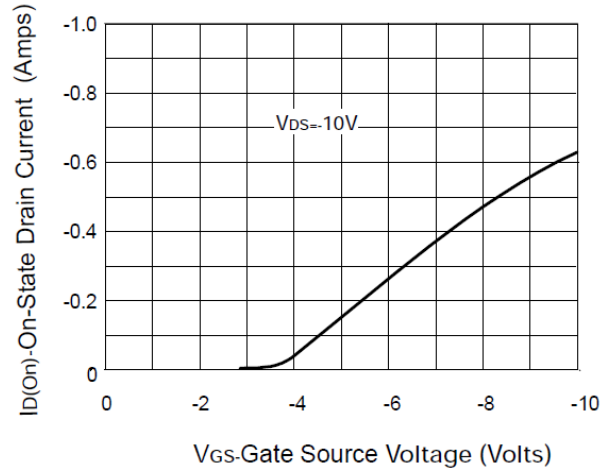
Output Characteristics



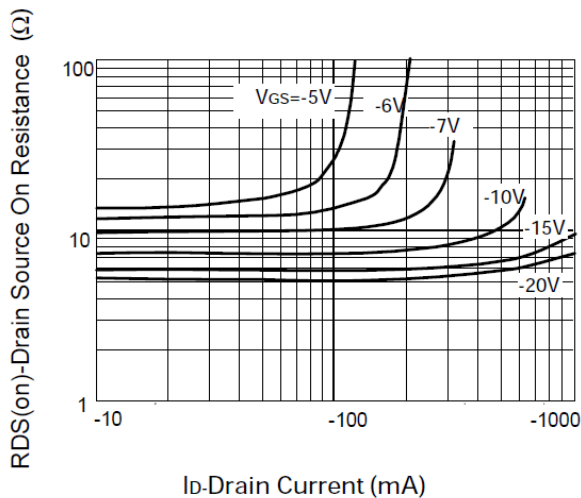
Saturation Characteristics



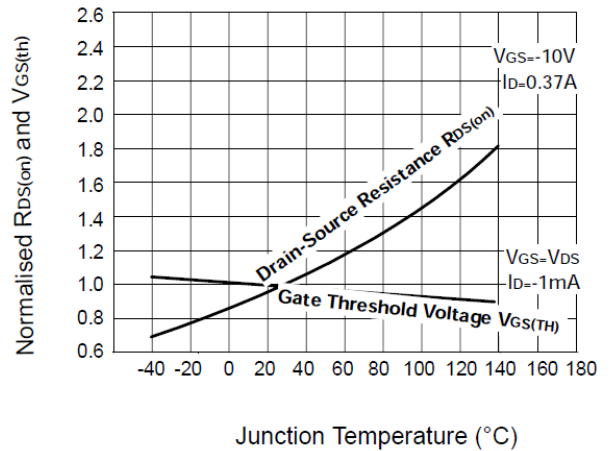
Voltage Saturation Characteristics



Transfer Characteristics

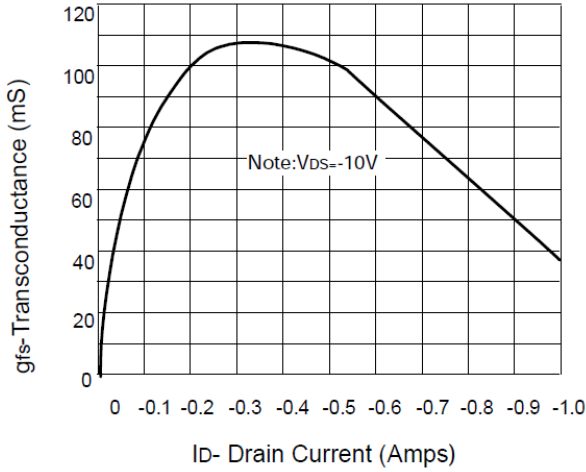


On-resistance vs Drain Current

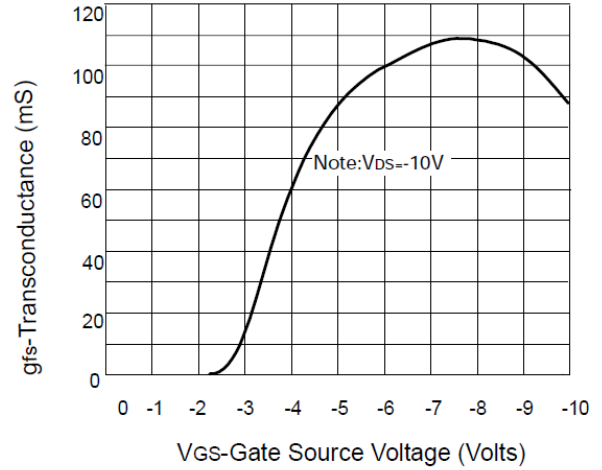


Normalised $R_{DS(on)}$ and $V_{GS(th)}$ vs Temperature

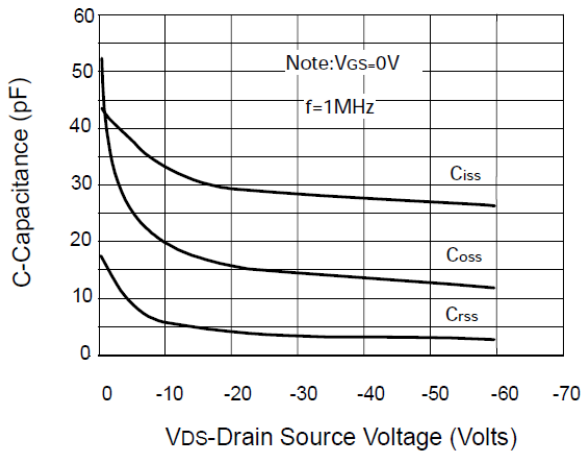
Typical Characteristics (continued)



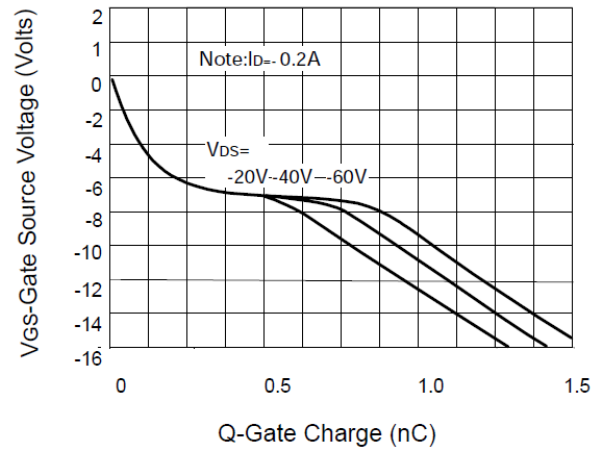
Transconductance v drain current



Transconductance v gate-source voltage



Capacitance v drain-source voltage



Gate charge v gate-source voltage

IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

A. Life support devices or systems are devices or systems which:

1. are intended to implant into the body, or
2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2019, Diodes Incorporated

www.diodes.com